

Cancelled

Title: POWER MOSFET, P-CHANNEL, RADIATION HARDENED,
HIGH RELIABILITY, SPACE USE,
DETAIL SPECIFICATION FOR
(JAXA R
2SJ1A01, 2SJ1A02, 2SJ1A03,
2SJ1A04, 2SJ1A05, 2SJ1A06,
2SJ1A07, 2SJ1A08, 2SJ1A09,
2SJ1A10, 2SJ1A11, 2SJ1A12)

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RADIATION HARDENED,
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DETAIL SPECIFICATION FOR

JAXA R
2SJ1A01, 2SJ1A02, 2SJ1A03
2SJ1A04, 2SJ1A05, 2SJ1A06
2SJ1A07, 2SJ1A08, 2SJ1A09
2SJ1A10, 2SJ1A11, 2SJ1A12

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This document is the English version of JAXA QTS/ADS which was originally written and authorized in Japanese and carefully translated into English for international users. If any question arises as to the context or detailed description, it is strongly recommended to verify against the latest official Japanese version.

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Rev.	Date	Description
NC	21 June 2011	Original
A	18 March 2020	▪ Cover: Changed the corporate name. ▪ Paragraph 3.2.1: Added marking for inspection lot identification code and serial number. ▪ Modified the wording in each paragraph in the document. ▪ Table 2a Group B inspection (B-3g) and Table 2b Group B inspection (B-6g): Corrected test condition error of Bond strength from "condition A" to "condition D".

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POWER MOSFET, P-CHANNEL, RADIATION HARDENED, HIGH RELIABILITY, SPACE USE, DETAIL SPECIFICATION FOR

JAXA R

2SJ1A01, 2SJ1A02, 2SJ1A03

2SJ1A04, 2SJ1A05, 2SJ1A06

2SJ1A07, 2SJ1A08, 2SJ1A09

2SJ1A10, 2SJ1A11, 2SJ1A12

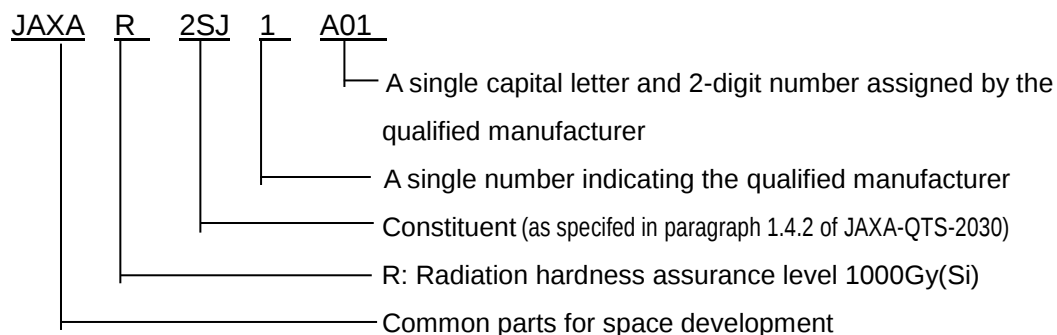
1 GENERAL

This specification establishes the detailed requirements for space use, high reliability, P channel power MOSFET (100 and 200V for TO-254 types and SMD types) used for electronic equipment installed on spacecrafts. The details for the products specified in this specification are as follows.

1.1 Part Number

The part numbers for the products are provided in accordance with JAXA-QTS-2030 and shall be shown as the following example.

(Example)



The part numbers for the products covered by this specification are assigned as follows:

JAXA R 2SJ1A01
 JAXA R 2SJ1A02
 JAXA R 2SJ1A03
 JAXA R 2SJ1A04
 JAXA R 2SJ1A05
 JAXA R 2SJ1A06
 JAXA R 2SJ1A07
 JAXA R 2SJ1A08
 JAXA R 2SJ1A09
 JAXA R 2SJ1A10
 JAXA R 2SJ1A11
 JAXA R 2SJ1A12

1.2 Absolute Maximum Ratings

The absolute maximum ratings of the products specified in this specification are as follows.

Unless otherwise specified, T_A is +25°C.

Part No.	V_{DS} (V)	I_D (A)	$I_{D(pulse)}$ (A)	V_{GS} (V)	P_D $T_C=25^\circ\text{C}$ (W)	P_D $T_A=25^\circ\text{C}$ (W)	$T_{ch}^{(1)}$ (°C)	T_{stg} (°C)	$R_{th(ch-c)}$ (°C/W)	$R_{th(ch-a)}$ (°C/W)	SOA
JAXA R 2SJ1A01	-100	-42	-168	±20	250 Fig.5	2.60 Fig.6	150	-55 to 150	0.5	48.0	Fig.7
JAXA R 2SJ1A02	-100	-25	-100		125 Fig.8	2.58 Fig.9			1.0	48.5	Fig.10
JAXA R 2SJ1A03	-100	-11	-44		62.5 Fig.11	2.55 Fig.12			2.0	49.0	Fig.13
JAXA R 2SJ1A04	-100	-42	-168		250 Fig.14	--- ---			0.5	---	Fig.15
JAXA R 2SJ1A05	-100	-29	-116		150 Fig.16	--- ---			0.83	---	Fig.17
JAXA R 2SJ1A06	-100	-13	-52		70 Fig.18	--- ---			1.67	---	Fig.19
JAXA R 2SJ1A07	-200	-35	-140		250 Fig.20	2.60 Fig.21			0.5	48.0	Fig.22
JAXA R 2SJ1A08	-200	-16	-64		125 Fig.23	2.58 Fig.24			1.0	48.5	Fig.25
JAXA R 2SJ1A09	-200	-7.5	-30		62.5 Fig.26	2.55 Fig.27			2.0	49.0	Fig.28
JAXA R 2SJ1A10	-200	-37	-148		250 Fig.29	--- ---			0.5	---	Fig.30
JAXA R 2SJ1A11	-200	-18	-72		150 Fig.31	--- ---			0.83	---	Fig.32
JAXA R 2SJ1A12	-200	-8.5	-34		70 Fig.33	--- ---			1.67	---	Fig.34

Note⁽¹⁾ The channel temperature T_{ch} is given by the following equations:

$$T_{ch}=T_C + R_{th(ch-c)} \times P_D$$

$$T_{ch}=T_A + R_{th(ch-a)} \times P_D$$

Where T_C : Case temperature (°C)

T_A : Ambient temperature (°C)

$R_{th(ch-c)}$: Thermal resistance between channel and case (°C/W)

$R_{th(ch-a)}$: Thermal resistance between channel and ambient (°C/W)

P_D : Power dissipation (W)

1.3 Primary Electrical Characteristics

The primary electrical characteristics of the products specified in this specification are as follows. Unless otherwise specified, T_A is +25°C.

Electrical Characteristics (1/3)

Part No.	$V_{(BR)DSS}$ (V)	I_{DSS} (μ A)	I_{GSS} (nA)	$V_{GS(th)}$ (V)	$R_{DS(on)}^{(1)}$ (m Ω)	$gfs^{(1)}$ (S)	E_{AS} (mJ)
	$I_D = -1mA$ $V_{GS} = 0V$	$V_{DS} = 80\%$ of rated V_{DS} $V_{GS} = 0V$	$V_{GS} = \pm 20V$ $V_{DS} = 0V$	$I_D = -1mA$ $V_{DS} = V_{GS}$	$I_D = 50\%$ of rated I_D $V_{GS} = -12V$	$I_D = 50\%$ of rated I_D $V_{DS} = -25V$	Rated I_D $V_{DD} = -48V$, $V_{GS} = -12V$
	Min	Max	Max	Min-Max	Max	Min	Max
JAXA R 2SJ1A01	-100	-10	± 100	-2.5 to -4.5	45	8	1091
JAXA R 2SJ1A02	-100				97	8	458
JAXA R 2SJ1A03	-100				226	4	260
JAXA R 2SJ1A04	-100				38	8	1426
JAXA R 2SJ1A05	-100				90	8	598
JAXA R 2SJ1A06	-100				219	4	391
JAXA R 2SJ1A07	-200				91	8	655
JAXA R 2SJ1A08	-200				210	8	358
JAXA R 2SJ1A09	-200				487	3.5	191
JAXA R 2SJ1A10	-200				84	8	809
JAXA R 2SJ1A11	-200				203	8	482
JAXA R 2SJ1A12	-200				480	3.5	299

Note⁽¹⁾ Pulse test: Pulse width $\leq 1ms$, Duty cycle $\leq 2\%$

Electrical Characteristics (2/3)

Part No.	Q_{GS} (nC)	Q_{GD} (nC)	Q_G (nC)	$t_{d(on)}$ (ns)	t_r (ns)	$t_{d(off)}$ (ns)	t_f (ns)
	$V_{DS}=50\%$ of rated V_{DS} , I_D = rated I_D , $V_{GS}=-12V$			$V_{DD}=50\%$ of rated V_{DS} , I_D = rated I_D , $V_{GS}=-12V$, $R_G=10\Omega$			
	Max	Max	Max	Max	Max	Max	Max
JAXA R 2SJ1A01	75	50	230	70	60	225	150
JAXA R 2SJ1A02	30	20	95	50	25	115	45
JAXA R 2SJ1A03	15	10	40	25	20	75	25
JAXA R 2SJ1A04	75	50	230	70	60	225	150
JAXA R 2SJ1A05	30	20	95	50	25	115	45
JAXA R 2SJ1A06	15	10	40	25	20	75	25
JAXA R 2SJ1A07	75	50	230	70	60	225	150
JAXA R 2SJ1A08	30	20	95	50	25	115	45
JAXA R 2SJ1A09	15	10	40	25	20	75	25
JAXA R 2SJ1A10	75	50	230	70	60	225	150
JAXA R 2SJ1A11	30	20	95	50	25	115	45
JAXA R 2SJ1A12	15	10	40	25	20	75	25

Electrical Characteristics (3/3)
(Body Diode Characteristics)

Part No.	$V_{SD}^{(1)}$ (V)	t_{rr} (ns)	Q_{rr} (μC)
	$I_F = \text{rated } I_D$ $V_{GS} = 0V$	$I_F = \text{rated } I_D, V_{GS} = 0V,$ $-di/dt = 100A/\mu s,$ $T_{ch} = 25^\circ C$	
	Max	Typ	Typ
JAXA R 2SJ1A01	-2.0	260	2.0
JAXA R 2SJ1A02		255	2.0
JAXA R 2SJ1A03		215	1.5
JAXA R 2SJ1A04		260	2.0
JAXA R 2SJ1A05		255	2.0
JAXA R 2SJ1A06		215	1.5
JAXA R 2SJ1A07		375	4.5
JAXA R 2SJ1A08		315	3.0
JAXA R 2SJ1A09		280	2.5
JAXA R 2SJ1A10		375	4.5
JAXA R 2SJ1A11		315	3.0
JAXA R 2SJ1A12		280	2.5

Note⁽¹⁾ Pulse test: Pulse width $\leq 1ms$, Duty cycle $\leq 2\%$

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1.4 Radiation Hardness

The radiation hardness of the products specified in this specification is as follows.

Symbol	Radiation hardness assurance level
R	1000 Gy(Si) { 1×10^5 rad(Si)} (Dose Rate 36Gy(Si)/ h to 360Gy(Si)/ h)

2 APPLICABLE DOCUMENTS

The latest issues of documents listed below at the time of contract award or application form a part of this specification the extent specified herein.

JAXA-QTS-2030	Semiconductor Devices, High Reliability, Space Use, General Specification for
MIL-STD-750	Test Methods Standard for Semiconductor Devices

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3 REQUIREMENTS

3.1 Design and Construction

The design and construction of the products shall meet this paragraph and paragraph 3.3 of JAXA-QTS-2030.

3.1.1 Package Configuration and Terminal Connection

The package configuration and terminal connection shall meet the requirements specified in Figures 1a, 1b, 1c and 1d.

3.1.2 Terminal Materials and Finish

a) TO-254 Package

The leads shall be made of Fe-Ni (Ni-Au plating) covered OCF (Oxygen-Free Copper) and plated with gold as specified in paragraph 3.3.7 c) 2) 2.3) or with Pb-Sn solder dipping as specified in paragraph 3.3.7 c) 2) 2.1) of JAXA-QTS-2030.

b) SMD Package

The material of terminals shall be Cu-W alloy. The terminals shall be finished with gold plating.

The purity of gold shall be a minimum of 99.7%. The thickness of the plating shall be a minimum of 1.27µm. This finish shall be plated with nickel as an underplating of a thickness between 1.27µm and 7.62µm.

3.1.3 Electrical Characteristics

The electrical characteristics shall meet the requirements specified in Tables 1a and 1b.

3.2 Marking

Marking shall be in accordance with the paragraph 3.4 of JAXA-QTS-2030 and Figures 2a, 2b, 2c and 2d.

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3.2.1 Marking for Inspection Lot Identification Code and Serial Number

The marking for inspection lot identification code and serial number shall be as follows.

Example:

19	01	001
a)	b)	c)
		
Inspection lot identification code		Serial number

- a) The last two digit number indicating the year the inspection started
- b) The two digit number indicating the week of sealing for the first inspection subplot (production lot) of each inspection lot. The week number is counted from the first week of January of the year
- c) Unique three-digit number from 001 to 999 consecutively assigned for each product within the inspection lot

3.3 Certification

The requirements for the products to be certified shall be in accordance with paragraph 3.1 of JAXA-QTS-2030.

4 QUALITY ASSURANCE PROVISIONS

4.1 General Requirements

The general requirements shall be in accordance with the paragraph 4.1 of JAXA-QTS-2030.

4.2 Incoming Materials Control

The incoming materials control shall be in accordance with the paragraph 4.2 of JAXA-QTS-2030.

4.3 Manufacturing Process Control

The manufacturing process control shall be in accordance with the paragraph 4.3 of JAXA-QTS-2030.

4.4 In-process Inspection

The in-process inspection shall be in accordance with the paragraph 4.5 of JAXA-QTS-2030.

4.5 Screening

The screening shall be in accordance with paragraph 4.7 of JAXA-QTS-2030. The electrical characteristics to be measured, test conditions and delta limits shall be as follows.

4.5.1 Electrical Characteristics to be Measured

The following parameters shall be measured during the interim and final electrical characteristics tests for screening.

(1) Interim electrical characteristic tests

$T_A = +25^\circ\text{C}$

Measuring item	$V_{(BR)DSS}$ (V)	I_{DSS} (μA)	I_{GSS} (nA)	$V_{GS(th)}$ (V)	$R_{DS(on)}^{(1)}$ ($\text{m}\Omega$)	$G_{FS}^{(1)}$ (S)	$V_{SD}^{(1)}$ (V)
MIL-STD-750 Test Method No.	3407	3413	3411	3404	3421	3475	---
Test conditions	Bias Condition C $I_D = -1\text{mA}$ $V_{GS} = 0\text{V}$	Bias Condition C $V_{DS} = 80\%$ of rated V_{DS} $V_{GS} = 0\text{V}$	Bias Condition C $V_{GS} = \pm 20\text{V}$ $V_{DS} = 0\text{V}$	$I_D = -1\text{mA}$ $V_{DS} = V_{GS}$	$I_D = 50\%$ of rated I_D $V_{GS} = -12\text{V}$	$I_D = 50\%$ of rated I_D $V_{DS} = -25\text{V}$	$I_F = \text{rated } I_D$ $V_{GS} = 0\text{V}$
	Min	Max	Max	Min-Max	Max	Min	Max
JAXA R 2SJ1A01	-100	-10	± 100	-2.5 to -4.5	45	8	-2.0
JAXA R 2SJ1A02	-100				97	8	
JAXA R 2SJ1A03	-100				226	4	
JAXA R 2SJ1A04	-100				38	8	
JAXA R 2SJ1A05	-100				90	8	
JAXA R 2SJ1A06	-100				219	4	
JAXA R 2SJ1A07	-200				91	8	
JAXA R 2SJ1A08	-200				210	8	
JAXA R 2SJ1A09	-200				487	3.5	
JAXA R 2SJ1A10	-200				84	8	
JAXA R 2SJ1A11	-200				203	8	
JAXA R 2SJ1A12	-200				480	3.5	

Note⁽¹⁾ Pulse test: Pulse width $\leq 1\text{ms}$, Duty cycle $\leq 2\%$

(2) Final electrical characteristics test: As specified in the subgroups 1, 2 and 3 of Tables 1a and 1b.

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4.5.2 Test Conditions

The conditions of gate stress test, avalanche energy test, temperature cycling test, reverse bias burn-in test and burn-in test for screening test shall be as follows.

(Gate stress test shall be performed as part of In-process inspection.)

Gate stress test: $V_{GS}=-35V$, $t=1ms$, $T_A=25^{\circ}C$

Single pulse avalanche energy (E_{AS}) test: $I_{D(pulse)} = \text{rated } I_D$, $V_{DD}=-48V$, $V_{GS}=-12V$

Initial $T_C = +25_{-5}^{+10}^{\circ}C$

$$L(mH) = \left[\frac{2E_{AS}}{(I_D)^2} \right] \left[\frac{BV_{DSS} - V_{DD}}{BV_{DSS}} \right] \quad \bullet \bullet \text{ Equation (1)}$$

Temperature cycling test: Condition G, 20 cycles

Reverse bias burn-in test (GS): $T_A=150^{\circ}C$, $V_{GS}=-16V$

$V_{DS}=0V$, 48hr

Burn-in test (DS): $T_A=150^{\circ}C$, $V_{DS}=80\%$ of rated V_{DS}

$V_{GS}=0V$, 240hr

4.5.3 Delta Limits

The delta limits for reverse bias burn-in test and burn-in test shall be as follows.

$$\Delta I_{GSS} \leq |20nA|$$

$$\Delta I_{DSS} \leq |10\mu A|$$

$$\Delta R_{DS(on)} \leq |20\%|$$

$$\Delta V_{GS(th)} \leq |20\%|$$

4.6 Qualification Test and Quality Conformance Inspection

The qualification test and the quality conformance inspection shall be in accordance with paragraphs 4.6 and 4.8 of JAXA-QTS-2030. External dimensions, electrical characteristics, test conditions and limits shall be as specified in Figures 1 and 3, and Tables 1, 2, 3, 4 and 5. Group C tests and Group D tests may be exempted when the qualification test or quality conformance inspection for the Groups C and D tests was performed and the device passed the test within a year. Detailed requirements are specified in Table 6.

Group E tests may be exempted in spite of chip size, when the semiconductor devices manufactured from the die of the same wafer lot have passed the Group E tests in the qualification test or the quality conformance inspection.

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4.6.1 Electrostatic Discharge Sensitivity Test

Electrostatic discharge sensitivity test in the qualification test shall be performed with the following lead combination:

Gate and Source

4.6.2 Radiation Hardness Test

Radiation test (TID: Total Dose Irradiation) level, electrical characteristics, test conditions and limits in the qualification tests and the quality conformance inspections shall be as specified in Table 5. The bias shall be maintained during the irradiation and post-irradiation electrical characteristics test. The post-irradiation electrical characteristics test shall be performed within 24 hours after the completion of irradiation.

4.7 Change of Tests and Inspections

No change has been made to any test or inspection specified in appendixes A, B or C of JAXA-QTS -2030.

4.8 Shipment after Long-term Storage

Shipment of the products stored at the manufacturer's site for 24 months or longer shall be in accordance with paragraph 4.9.1 of JAXA-QTS-2030.

5 PREPARATION FOR DELIVERY

Preparation for delivery shall be in accordance with Section 5 of JAXA-QTS-2030.

6 NOTES

6.1 Terms and Definitions

The terms and definitions used herein shall be in accordance with paragraph 1.2 of JAXA-QTS-2030 and as follows.

(1) SEB (Single Event Burnout);

Burnout of the device caused by the incidence of a proton or a heavy ion, when the device is applied to an off-state voltage between drain and source.

(2) SEGR (Single Event Gate Rupture);

Breakdown of MOSFET Gate Oxide film caused by the incidence of a proton or a heavy ion, when the device is applied to a gate bias voltage between gate and source.

6.2 Notes for Purchasers

The precautions to be taken by the purchaser shall be in accordance with paragraph 6.2 of JAXA-QTS-2030 and as follows.

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6.2.1 Handling Instructions

The products specified in this specification contain thin oxide films and can be damaged due to electrostatic discharge (ESD). ESD protection measures shall be implemented to avoid ESD between the gate and source and between the gate and drain during transportation and other handling environments.

6.2.2 Beryllium Warning

The products specified in this specification contain beryllium. Disintegration or chemical processing of the products that may produce dusts or fumes shall be prohibited. Disposition of the products shall be performed in accordance with applicable regulations. (Beryllium is used in 2SJ1A01, 2SJ1A02, 2SJ1A03, 2SJ1A07, 2SJ1A08 and 2SJ1A09)

Table 1a. Group A Inspection ⁽¹⁾

Gr.No	MIL-STD-750				100V Class						200V Class					
	Sub	Test Item	Method	JAXA R	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12
A -1	Static Characteristics (T _A =25°C)			Sample Size	LTPD 3											
	-1a	Breakdown Voltage Drain to Source V _{DSS}	3407	Conditions	Bias Condition C I _D =-1mA , V _{GS} =0V											
				Limits	min -100V DC						min -200V DC					
	-1b	Gate Current I _{GSS}	3411	Conditions	Bias Condition C V _{GS} =±20V , V _{DS} =0V											
				Limits	max ±100nA DC											
	-1c	Drain Current I _{DSS}	3413	Conditions	Bias Condition C V _{DS} =-80V , V _{GS} =0V						Bias Condition C V _{DS} =-160V , V _{GS} =0V					
				Limits	max -10μA DC											
	-1d	Gate to Source Voltage (Threshold) V _{GS(th)}	3404	Conditions	Bias Condition C V _{GS} =V _{DS} , I _D =-1mA											
				Limits	-2.5 to - 4.5V DC											
	-1e	Static Drain to Source On-State Resistance R _{DS(on)}	3421	Conditions	Pulse Test ⁽²⁾ , V _{GS} =-12V											
				I _D -21A -12.5A -5.5A -21A -14.5A -6.5A						I _D -17.5A -8A -3.75A -18.5A -9A -4.25A						
				max [mΩ] 45 97 226 38 90 219						max [mΩ] 91 210 487 84 203 480						
	-1f	Forward Transconductance g _{fs}	3475	Conditions	Pulse Test ⁽²⁾ , V _{DS} =-25V											
				I _D -21A -12.5A -5.5A -21A -14.5A -6.5A						I _D -17.5A -8A -3.75A -18.5A -9A -4.25A						
				min 8S 8S 4S 8S 8S 4S						min 8S 8S 3.5S 8S 8S 3.5S						
	-1g	Forward Voltage V _{SD}	---	Conditions	Pulse Test ⁽²⁾ , V _{GS} =0V											
				I _D -42A -25A -11A -42A -29A -13A						I _D -35A -16A -7.5A -37A -18A -8.5A						
				max -2.0V DC												
A -2	Static Characteristics (T _A =125°C)			Sample Size	LTPD 5											
	-2a	Gate Current I _{GSS} (125°C)	3411	Conditions	Bias Condition C V _{GS} =±20V , V _{DS} =0V											
				Limits	max ±100nA DC											
	-2b	Drain Current I _{DSS} (125°C)	3413	Conditions	Bias Condition C V _{DS} =-80V , V _{GS} =0V						Bias Condition C V _{DS} =-160V , V _{GS} =0V					
				Limits	max -25μA DC											
	-2c	Gate to Source Voltage (Threshold) V _{GS(th)} (125°C)	3404	Conditions	Bias Condition C V _{GS} =V _{DS} , I _D =-1mA											
				Limits	min -2.0V DC											
	-2d	Static Drain to Source On-State Resistance R _{DS(on)} (125°C)	3421	Conditions	Pulse Test ⁽²⁾ , V _{GS} =-12V											
				I _D -21A -12.5A -5.5A -21A -14.5A -6.5A						I _D -17.5A -8A -3.75A -18.5A -9A -4.25A						
				max [mΩ] 78 168 392 66 156 380						max [mΩ] 183 422 979 169 408 965						

Notes ⁽¹⁾ The same sample may be used for all subgroups.

⁽²⁾ Pulse test: Pulse width ≤ 1ms, Duty cycle ≤ 2%

Table 1b. Group A Inspection ⁽¹⁾

Gr.No		MIL-STD-750			100V Class						200V Class					
	Sub	Test Item	Method	JAXA R	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12
A -3	Static Characteristics (T _A =-55°C)			Sample Size	LTPD 5											
	-3a	Gate to Source Voltage (Threshold) V _{GS(th)} (-55°C)	3404	Conditions	Bias Condition C V _{GS} =V _{DS} , I _D =-1mA											
				Limits	max -5.0V DC											
	-3b	Forward Transconductance g _{fs} (-55°C)	3475	Conditions	Pulse Test ⁽²⁾ , V _{DS} =-25V											
				Limits	I _D -21A -12.5A -5.5A -21A -14.5A -6.5A min 8.5S 8.5S 4.5S 8.5S 8.5S 4.5S						I _D -17.5A -8A -3.75A -18.5A -9A -4.25A min 8.5S 8.5S 4.0S 8.5S 8.5S 4.0S					
A -4	Dynamic Characteristics (T _A =25°C)			Sample Size	LTPD 3											
	Switching Time Test (1) Turn-on delay time: t _{d(on)} Rise time: t _r (2) Turn-off delay time: t _{d(off)} Fall time: t _f	3472	Conditions	V _{DD} =-50V V _{GS} =-12V, R _g =10Ω I _D -42A -25A -11A -42A -29A -13A						V _{DD} =-100V V _{GS} =-12V, R _g =10Ω I _D -35A -16A -7.5A -37A -18A -8.5A						
			Limits	max 70 50 25 70 50 25 60 25 20 60 25 20 225 115 75 225 115 75 150 45 25 150 45 25						max 70 50 25 70 50 25 60 25 20 60 25 20 225 115 75 225 115 75 150 45 25 150 45 25						
			t _{d(on)}	70	50	25	70	50	25	70	50	25	70	50	25	
			t _r	60	25	20	60	25	20	60	25	20	60	25	20	
			t _{d(off)}	225	115	75	225	115	75	225	115	75	225	115	75	
			t _f	150	45	25	150	45	25	150	45	25	150	45	25	
A -6a	Safe Operating Area Test ⁽³⁾			Sample Size	LTPD 5											
			3474	Conditions	---											
	-6b	End-Point Electrical Measurements		---		Same as Gr.A-1										
A -7	Other Characteristics (T _A =25°C) ⁽⁴⁾			Sample Size	LTPD 10											
	-7a	Gate Charge (1) Gate Charge: Q _g (2) Gate to Drain Charge: Q _{gd} (3) Gate to Source Charge: Q _{gs}	3471	Conditions	V _{GS} =-12V V _{DS} =-50V I _D -42A -25A -11A -42A -29A -13A						V _{GS} =-12V V _{DS} =-100V I _D -35A -16A -7.5A -37A -18A -8.5A					
				Limits	max 230nC 95nC 40nC 230nC 95nC 40nC 50nC 20nC 10nC 50nC 20nC 10nC 75nC 30nC 15nC 75nC 30nC 15nC						max 230nC 95nC 40nC 230nC 95nC 40nC 50nC 20nC 10nC 50nC 20nC 10nC 75nC 30nC 15nC 75nC 30nC 15nC					
				Q _g	230nC	95nC	40nC	230nC	95nC	40nC	230nC	95nC	40nC	230nC	95nC	40nC
				Q _{gd}	50nC	20nC	10nC	50nC	20nC	10nC	50nC	20nC	10nC	50nC	20nC	10nC
				Q _{gs}	75nC	30nC	15nC	75nC	30nC	15nC	75nC	30nC	15nC	75nC	30nC	15nC
	-7b	Reverse Recovery Characteristics (1) T _{rr} (2) Q _{rr}	3473	Conditions	I _F = I _D -42A -25A -11A -42A -29A -13A						I _F = I _D -35A -16A -7.5A -37A -18A -8.5A					
Limits				V _{GS} =0V -di/dt=100A/μs max 260 255 215 260 255 215 2.0 2.0 1.5 2.0 2.0 1.5						max 375 315 280 375 315 280 4.5 3.0 2.5 4.5 3.0 2.5						

Notes ⁽¹⁾ The same sample may be used for all subgroups.

⁽²⁾ Pulse test: Pulse width ≤ 1ms, Duty cycle ≤ 2%

⁽³⁾ The samples used for subgroups A-1, A-2, and A-3 tests shall be used.

⁽⁴⁾ The samples used for subgroups A-6 tests shall be used.

Table 2a. Group B Inspection

Gr.No	MIL-STD-750			JAXA R	100V Class						200V Class					
	Sub	Test Item	Method		2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12
B -1	Dimensions ⁽¹⁾		Sample Size	Level I ⁽²⁾ 3p Level II ⁽²⁾ 3p												
		2066	Conditions	See Fig. 1												
B -2	Resistance to Solvents ⁽³⁾ ⁽⁴⁾		Sample Size	Level I 3p Level II 3p												
		1022	Conditions	Solvent a, b, c												
B -3b	Temperature Cycling (Air to Air)		Sample Size	Level I 6p Level II 6p												
		1051	Conditions	$-55^{+0}_{-5}^{\circ}\text{C} \leftrightarrow 25^{+10}_{-5}^{\circ}\text{C} \leftrightarrow 150^{+5}_{-0}^{\circ}\text{C}$ 100 cycles												
-3c	Surge Test (1) Gate Shock	4066	Conditions	$V_{GS}=-35\text{V}$												
		(2) Avalanche	4066	Conditions	$V_{DS}=-48\text{V}$, L= See paragraph 4.5.2, Equation (1) $I_{D(\text{pulse})}$ -42A -25A -11A -42A -29A -13A -35A -16A -7.5A -37A -18A -8.5A											
-3d	Hermetic Seal (1) Fine	1071	Conditions	Condition H												
			Limits	max $1 \times 10^{-3} \text{Pa} \cdot \text{cm}^3/\text{s}$												
		(2) Gross	1071	Conditions	--- Condition C											
-3e	End-Point Electrical Measurements	---	Conditions	Same as Gr.A-1												
-3f	Decap-Internal Visual and mechanical inspection	2075 2071	Conditions	---												
-3g	Bond Strength	2037	Conditions	Condition D												
			Limits	Gate Wire >90gf Source Wire >300gf >300gf >90gf >300gf >300gf >90gf >300gf >300gf >90gf >300gf >300gf >90gf												
-3h	SEM ⁽¹⁾	2077	Conditions	---												
-3i	Die Shear		Sample Size	Level I 3p Level II 3p												
		2017	Conditions	---												
			Limits	min 2.5kgf												
B -4	Solderability ⁽³⁾ ⁽⁴⁾		Sample Size	Level I 6 leads ⁽⁵⁾ Level II 6 leads ⁽⁵⁾												
		2026	Conditions	---												

Notes ⁽¹⁾ The test may be performed using the samples prior to inspection lot formation.

⁽²⁾ Level I and Level II shall be applicable to the qualification test and the quality conformance inspection, respectively. (See paragraphs C.3.2 and C.3.3 of JAXA-QTS-2030)

⁽³⁾ Electrical reject products from the same inspection lot may be used.

⁽⁴⁾ When electrical reject products are used, the samples shall be exposed to the same thermal environments as the certified samples experience in all thermal tests required as part of the screening test.

⁽⁵⁾ This test shall be performed for each 3 lead from 2 devices.

Table 2b. Group B Inspection

Gr.No	MIL-STD-750				100V Class						200V Class					
	Sub	Test Item	Method		JAXA R	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11
B -5a	Intermittent Operation Life			Sample Size	Level I LTPD 10											
				1042	Conditions	Level II 12p										
					Condition D, 2000 cycles ⁽¹⁾											
-5b	End-Point Electrical Measurements		---	Conditions	Same as Gr.A-1											
B -6c	Accelerated Steady-state Gate Stress (High Temp. GS)			Sample Size	Level I LTPD 10											
				1042	Conditions	Level II 12p										
					V _{GS} =-20V, T _A =150°C, 48hr or V _{GS} =-20V, T _A =175°C, 24hr											
-6d	End-Point Electrical Measurements		---	Conditions	Same as Gr.A-1											
-6e	Accelerated Steady- state Reverse Bias (High Temp. DS)		1042	Conditions	V _{DS} =100V						V _{DS} =200V					
					T _A =150°C, 240hr or T _A =175°C, 120hr											
-6f	End-Point Electrical Measurements		---	Conditions	Same as Gr.A-1											
-6g	Bond Strength			Sample Size	20 wires											
				2037	Conditions	Condition D										
				Limits	Gate Wire											
					>90gf											
				Source Wire												
				>300gf >300gf >90gf >300gf >300gf >90gf >300gf >300gf >90gf >300gf >300gf >90gf												
B -7	Thermal Impedance Z _{th(ch-c)} (ΔV _{SD})			Sample Size	Level I LTPD 10											
				3161	Conditions	Level II 8p										
					T _A =25°C											
					max (°C/W)						max (°C/W)					
					0.5	1.0	2.0	0.5	0.83	1.67	0.5	1.0	2.0	0.5	0.83	1.67

Note⁽¹⁾ If the samples are also used for "Intermittent operating life test" of C1-1 in the Group C test, the test shall be performed up to 6000 cycles.

Table 3. Group C Inspection

Gr.No	MIL-STD-750				100V Class						200V Class						
	Sub	Test Item	Method		JAXA R	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12
C 1-1a	Intermittent Operation Life		Sample Size	Level I LTPD 10													
			Sample Size	Level II LTPD 10													
		1042	Conditions	Condition D, 6000 cycles ⁽¹⁾													
1-1b	End-Point Electrical Measurements	---	Conditions	Same as Gr.A-1													
C 1-2a	Steady-state Bias Life test (high temperature GS applied) ⁽²⁾		Sample Size	Level I LTPD 5													
			Sample Size	Level II NA													
		1042	Conditions	V _{GS} =-16V T _A =150°C , 1000hr													
1-2b	End-Point Electrical Measurements	---	Conditions	Same as Gr.A-1													
1-2c	Steady-state Bias Life test (high temperature DS applied) ⁽²⁾ ⁽³⁾		Sample Size	Level I LTPD 5													
			Sample Size	Level II NA													
		1042	Conditions	V _{DS} =80V V _{DS} =160V T _A =150°C, 1000hr													
1-2d	End-Point Electrical Measurements	---	Conditions	Same as Gr.A-1													
C -2a	Temperature Cycling		Sample Size	Level I 12p													
			Sample Size	Level II NA													
		1051	Conditions	-55 ⁺⁰ _{-.5} °C↔25 ⁺¹⁰ _{-.5} °C↔150 ⁺⁵ _{-.0} °C 100 cycles													
	-2b	Hermetic Seal (1) Fine	1071	Conditions	Condition H												
				Limits	max 1×10 ⁻³ Pa·cm ³ /s												
-2c	(2) Gross	1071	Conditions	Condition C													
			End-Point Electrical Measurements ⁽⁴⁾	---	Conditions	Same as Gr.A-1											
C -3	Thermal Impedance ⁽⁵⁾ ⁽⁶⁾ Z _{th(ch-c)} (ΔV _{SD})		Sample Size	Level I LTPD 10													
			Sample Size	Level II 8p													
		3161	Conditions	T _A =25°C													
		Limits	max (°C/W)						max (°C/W)								
			0.5	1.0	2.0	0.5	1.0	2.0	0.5	1.0	2.0	0.5	1.0	2.0			
C -4a	Safe Operating Area Test ⁽⁷⁾		Sample Size	Level I LTPD 10													
			Sample Size	Level II LTPD 10													
		3474	Conditions	---													
-4b	End-Point Electrical Measurements ⁽⁷⁾	---	Conditions	Same as Gr.A-1													
C -6a	Electric Discharge Sensitivity Classification		Sample Size	Level I 3p													
			Sample Size	Level II NA													
		1020	Conditions	V _{GS} ±2750V ±1000V ±500V ±2750V ±1000V ±500V ±2750V ±1000V ±500V ±2750V ±1000V ±500V V _{DS} =0V													
-6b	End-Point Electrical Measurements	---	Conditions	Same as Gr.A-1													

Notes ⁽¹⁾ For the quality conformance inspection, the minimum cycles may be reduced to 2000 cycles.

⁽²⁾ The legibility of the marking shall not apply.

⁽³⁾ This test may be conducted using the samples other than the ones used for Group C1-2a.

⁽⁴⁾ This test may be conducted prior to the hermetic seal.

⁽⁵⁾ Thermal impedance curve shall be obtained during the qualification test.

⁽⁶⁾ This test may be exempted if performed in the Group B test.

⁽⁷⁾ This test may be exempted if performed in the Group A test.

Table 4a. Group D Inspection

Gr.No	MIL-STD-750			100V Class						200V Class							
	Sub	Test Item	Method	JAXA R	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12	
D -1a	Thermal Shock (Glass Strain)		Sample Size	Level I LTPD 15													
				Level II LTPD 15													
		1056	Conditions	Condition B, 15 cycles													
	-1b	Temperature Cycling	1051	Conditions	-55 ⁺⁰ _{-.5} °C↔25 ⁺¹⁰ _{-.5} °C↔150 ⁺⁵ _{-.0} °C 45 cycles												
	-1c	Terminal Strength	2036	Conditions	Condition A 1.5kg, 30s												
	-1d	Moisture Resistance	1021	Conditions	(MIL-STD-202, Method 106)												
	-1e	Hermetic Seal (1) Fine	1071	Conditions	Condition H												
				Limits	max 1×10 ⁻³ Pa·cm ³ /s												
		(2) Gross	1071	Conditions	Condition C												
	-1f	Visual Inspection	1051 1021	Conditions	---												
1g	End-Point Electrical Measurements	---	Conditions	Same as Gr.A-1													
D -2a	Shock ⁽¹⁾		Sample Size	Level I LTPD 15													
					Level II LTPD 15												
		2016	Conditions	No Operating, 14700m/s ² (1500G) 5 blows in each orientation, X ₁ , Y ₁ , Y ₂ and Z ₁													
	-2b	Vibration, Variable Frequency ⁽¹⁾	2056	Conditions	100 to 2000 Hz, 4min 196 m/s ² (20G) 4 times each orientation, X, Y and Z												
	-2c	Constant Acceleration ⁽¹⁾	2006	Conditions	98100 m/s ² (10000G) X ₁ , Y ₁ , Y ₂ and Z ₁ orientation												
	-2d	Hermetic Seal ⁽¹⁾ (1) Fine	1071	Conditions	Condition H												
				Limits	max 1×10 ⁻³ Pa·cm ³ /s												
		(2) Gross	1071	Conditions	Condition C												
	-2e	End-Point Electrical Measurements ⁽¹⁾	---	Conditions	Same as Gr.A-1												
D -3a	Salt Atmosphere ⁽²⁾		Sample Size	Level I LTPD 15													
					Level II LTPD 15												
		1041	Conditions	35°C, 24hr Rate of salt deposit=10 to 50g/m ² /24hr													

Notes⁽¹⁾ Samples used for subgroup 1 may be used.

⁽²⁾ Electrical reject products from the same inspection lot may be used.

Table 4b. Group D Inspection

Gr.No	MIL-STD-750		JAXA R	100V Class						200V Class					
	Sub	Test Item	Method	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12
D -5		Internal Water Vapor (¹)	Sample Size	Level I 3p											
			1018	Level II 3p											
D -6a		Resistance to Soldering Heat	Conditions	---											
			2031	Level I 3p Level II NA											
-6b		Visual Inspection	Conditions	250°C, 10s											
			---	240°C, 10s											
-6c		Hermetic Seal (1) Fine	Conditions	250°C, 10s											
			Limits	240°C, 10s											
-6c		(2) Gross	Conditions	Condition H max 1×10⁻³Pa·cm³/s											
			1071	Condition C											
-6d		End-Point Electrical Measurements	---	Same as Gr.A-1											

Note(¹) Electrical reject products from the same inspection lot may be used.

Table 5. Group E Inspection

Gr.No	MIL-STD-750				100V Class						200V Class					
	Sub	Test Item	Method	JAXA R	2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A10	2SJ 1A11	2SJ 1A12
E -1a	Total Dose Irradiation (TID)		Sample Size	Level I 4p ⁽¹⁾												
		1019	Conditions	Level II 4p ⁽¹⁾												
-1b	End-Point Electrical Measurements			Total Dose 1×10 ³ Gy(Si) Dose Rate 36Gy(Si)/h to 360Gy(Si)/h												
				Bias Condition (during irradiation, after irradiation) (a) V _{DS} =0V , V _{GS} =-20V												
	(1)	Breakdown Voltage Drain to Source V _{DSS}	3407	Conditions	(b) V _{DS} =-80V, V _{GS} =0V						(b) V _{DS} =-160V, V _{GS} =0V					
					Limits	Within 24hr after irradiation										
	(2)	Gate Current I _{GSS}	3411	Conditions		Bias Condition C I _D =-1mA , V _{GS} =0V										
					Limits	min -100V DC						min -200V DC				
	(3)	Drain Current I _{DSS}	3413	Conditions		Bias Condition C V _{GS} =±20V , V _{DS} =0V										
					Limits	max ±100nA DC										
	(4)	Gate to Source Voltage (Threshold) V _{GS(th)}	3404	Conditions		Bias Condition C V _{DS} =-80V , V _{GS} =0V						Bias Condition C V _{DS} =-160V , V _{GS} =0V				
					Limits	max -10μA DC										
	(5)	Static Drain to Source On-State Resistance R _{DS(on)}	3421	Conditions		Bias Condition C V _{GS} =V _{DS} , I _D =-1mA										
					Limits	-2.5 to -4.5V DC										
				Conditions		Pulse Test ⁽²⁾ , V _{GS} =-12V										
					I _D						I _D					
					-21A	-12.5A	-5.5A	-21A	-14.5A	-6.5 A	-17.5A	-8A	-3.75A	-18.5A	-9A	-4.25A
			Limits	max [mΩ]						max [mΩ]						
				45	97	226	38	90	219	91	210	487	84	203	480	

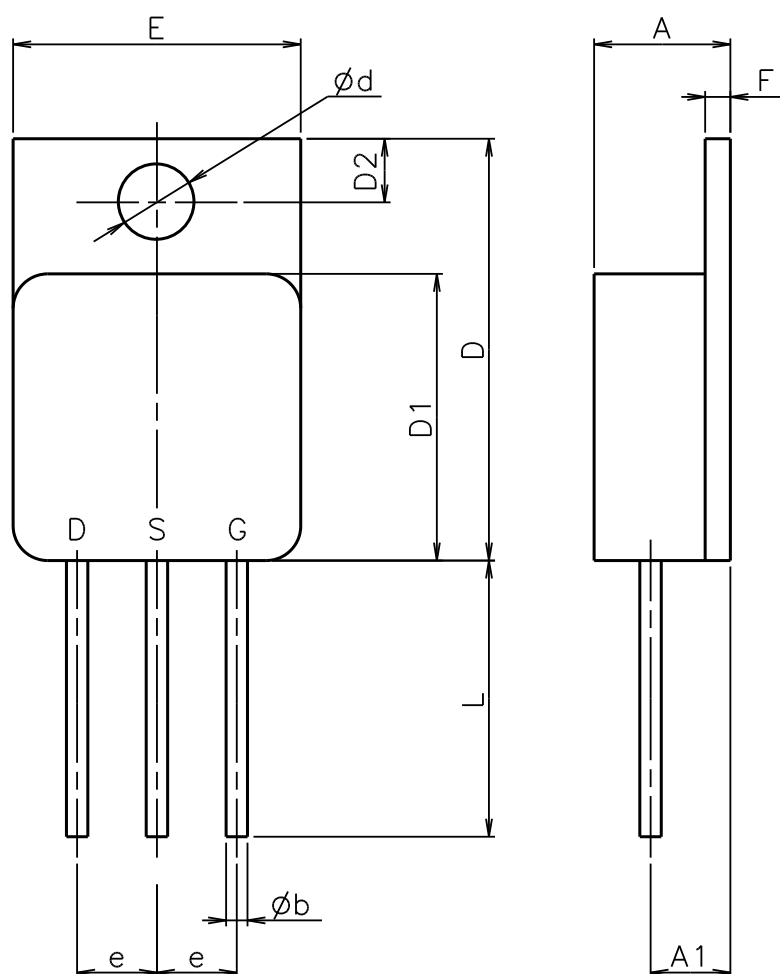
Notes ⁽¹⁾ This test shall be performed for each single wafer lot. When an inspection lot consists of multiple inspection sublots, one inspection subplot may be performed this test.

⁽²⁾ Pulse test: Pulse width ≤ 1ms, Duty cycle ≤ 2%

Table 6. Exemption of Quality Conformance Inspection

When the qualification test or the quality conformance inspection for products specified as following table was initiated within a year from the completion date of the screening test for the inspection lot, and the device passed the test or inspection, the corresponding tests may be exempted.

Gr.No	Package	TO-254						SMD-					
		100V Class			200V Class			100V Class			200V Class		
		2SJ 1A01	2SJ 1A02	2SJ 1A03	2SJ 1A07	2SJ 1A08	2SJ 1A09	2SJ 1A04	2SJ 1A05	2SJ 1A06	2SJ 1A10	2SJ 1A11	2SJ 1A12
Sub	JAXA R	1/1	1/2	1/4	1/1	1/2	1/4	1/1	1/2	1/4	1/1	1/2	1/4
	JAXA-QTS-2030 Appendix C Test Item	1/1	1/2	1/4	1/1	1/2	1/4	1/1	1/2	1/4	1/1	1/2	1/4
C	1-1a Intermittent Operation Life	The tests may be exempted when: 1) the devices having the same or larger die size have passed the tests. 2) the test is performed with the same or larger V _{DS} specified in paragraph 1.2.						The tests may be exempted when: 1) the devices having the same or larger die size have passed the tests. 2) the test is performed with the same or larger V _{DS} specified in paragraph 1.2.					
	1-1b End-Point Electrical Measurements												
	-2a Thermal Shock (Temperature Cycling)												
	-2b Hermetic Seal												
	-2c End-Point Electrical Measurements	This test may be exempted when the device passed the Group B-7 test.											
	-3 Thermal Resistance												
	-4a Safe Operating Area Test												
	-4b End-Point Electrical Measurements	This test may be exempted when the device passed the Group A-6 test.											
D	-1a Thermal Shock (Glass Strain)	This test may be exempted when any one of the products passed the Group D-1 test.						- The tests using the package types SMD-1 and SMD-0.5 may be exempted when SMD-2 has passed these tests. - The tests using the package type SMD-0.5 may be exempted when SMD-1 has passed these tests.					
	-1b Thermal Shock (Temperature Cycling)												
	-1c Terminal Strength												
	-1d Moisture Resistance												
	-1e Hermetic Seal												
	-1f Visual Inspection												
	-1g End-Point Electrical Measurements												
	-2a Shock												
	-2b Vibration, Variable Frequency												
	-2c Constant Acceleration												
	-2d Hermetic Seal												
	-2e End-Point Electrical Measurements												
	-3a Salt Atmosphere												
	-5 Internal Water Vapor							This test may be exempted when any one of the products passed the test.					

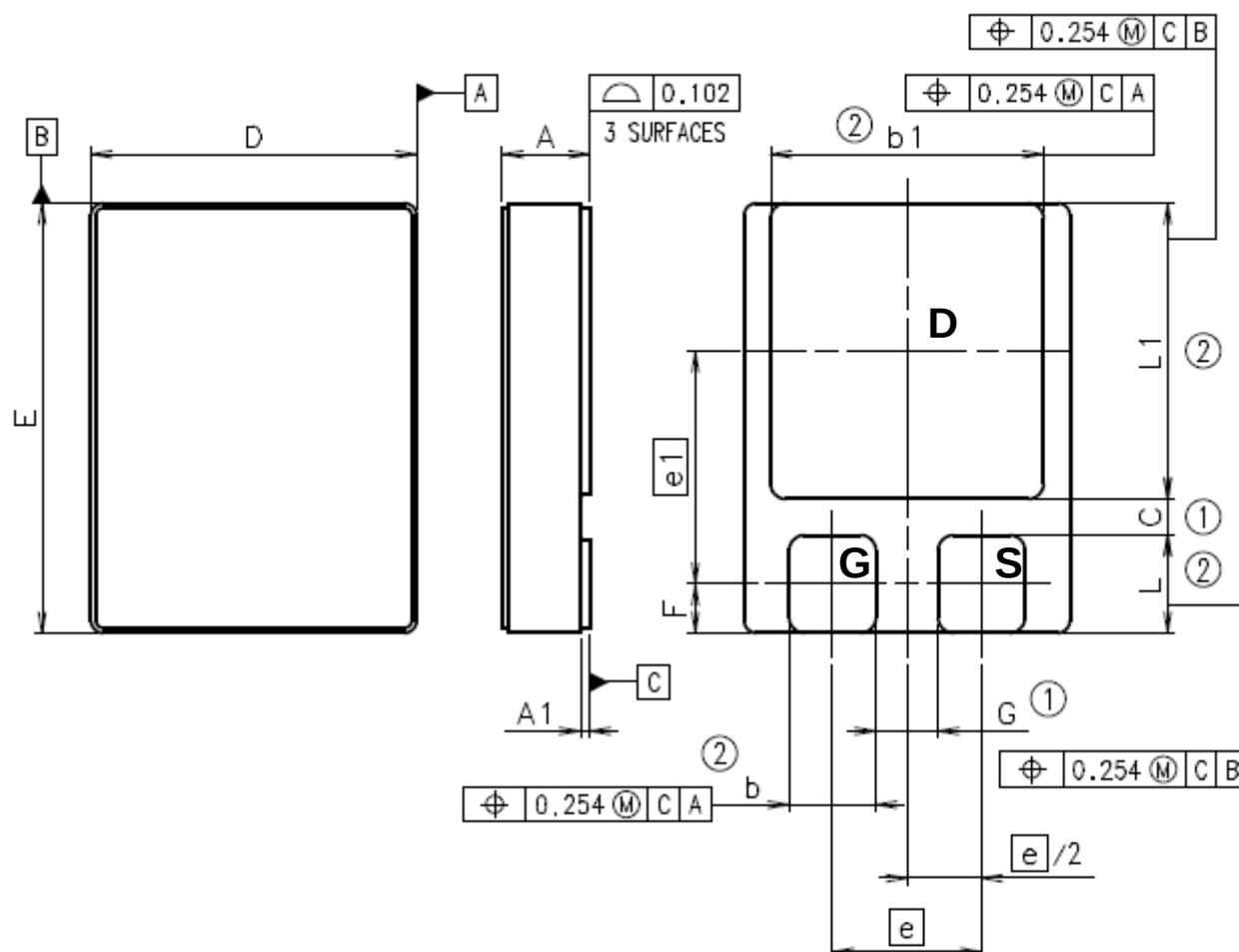


Symbol	Dimension (mm)	
	Min	Max
A	6.35	6.65
A1	3.61	4.01
ϕb	0.90	1.14
D	20.07	20.31
D1	13.59	13.85
D2	2.93	3.17

Symbol	Dimension (mm)	
	Min	Max
ϕd	3.56	3.80
E	13.60	13.84
e	3.51	4.11
F	1.10	1.30
L	12.84	13.60

Note: All leads are isolated from the case.

Figure 1a. Package Configuration and Lead Connection of TO-254 Type Package
(JAXA R 2SJ1A01, 2SJ1A02, 2SJ1A03, 2SJ1A07, 2SJ1A08 and 2SJ1A09)



Symbol	Dimension (mm)		
	Min	Typ	Max
A	—	—	3.58
A1	0.254	0.381	0.508
b	3.43	3.555	3.68
b1	11.05	11.175	11.30
C	0.89	—	—
D	13.21	13.335	13.46
E	17.40	17.525	17.65

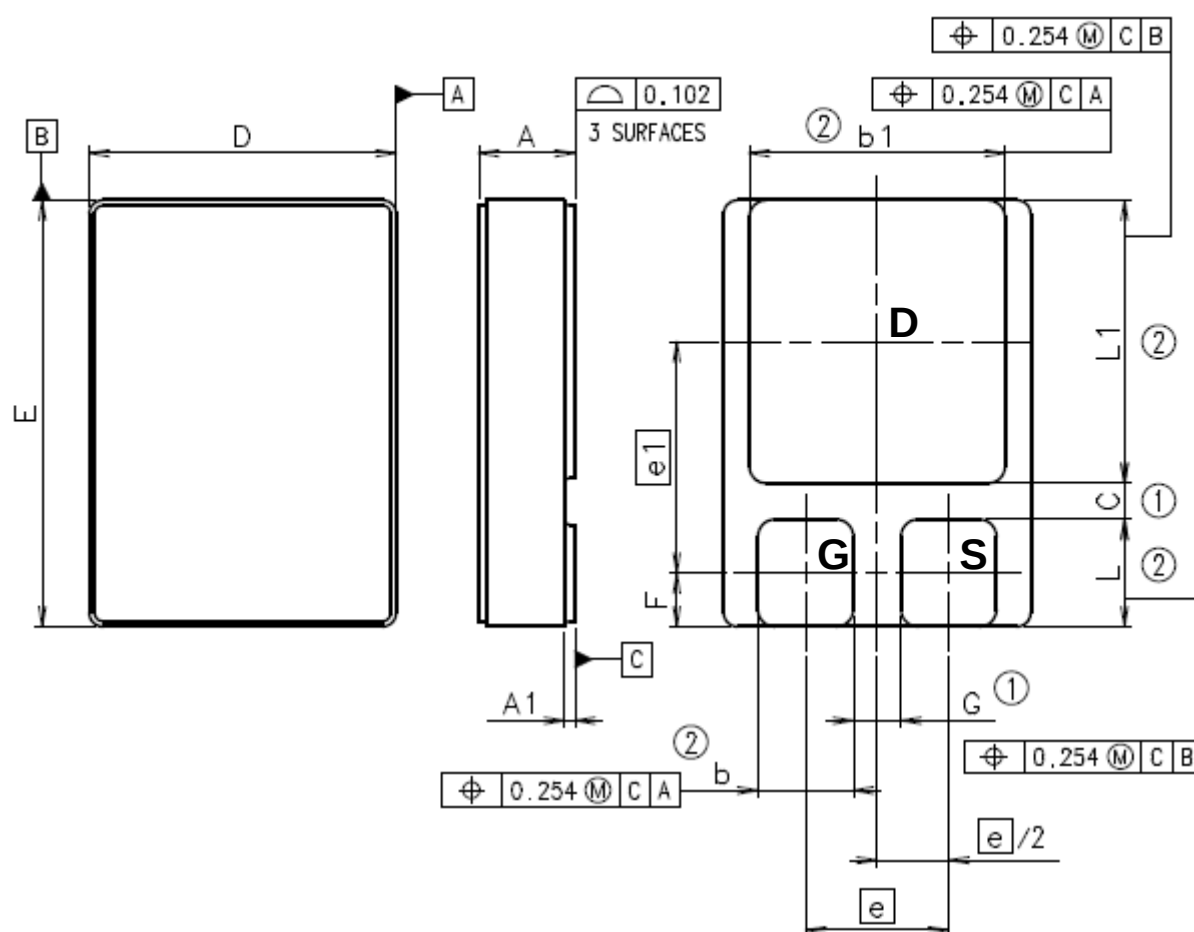
Symbol	Dimension (mm)		
	Min	Typ	Max
$e/2$	—	3.05	—
e	—	6.10	—
$e1$	—	9.50	—
F	—	1.99	—
G	1.27	—	—
L	3.87	3.99	4.11
L1	11.94	12.065	12.19

Notes: ① Dimension includes metallization flash.

② Dimension does not include metallization flash.

Note: All terminals are isolated from the case.

Figure 1b. Package Configuration and Terminal Connection of SMD-2 Type Package
(JAXA R 2SJ1A04 and 2SJ1A10)



Symbol	Dimension (mm)		
	Min	Typ	Max
A	—	—	3.58
A1	0.254	0.381	0.508
b	3.43	3.555	3.68
b1	9.40	9.525	9.65
C	0.76	—	—
D	11.31	11.43	11.55
E	15.75	15.875	16.00

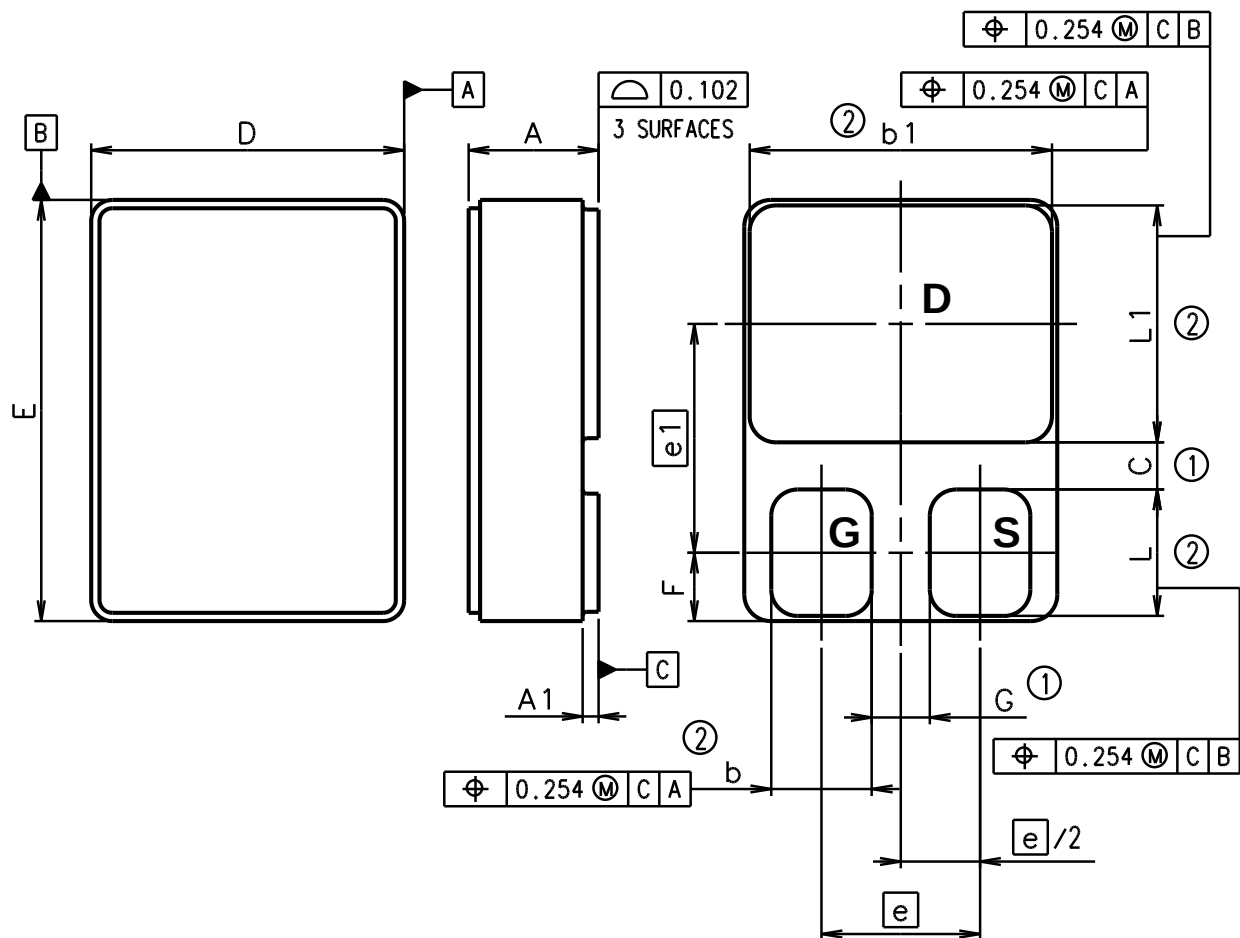
Symbol	Dimension (mm)		
	Min	Typ	Max
$e/2$	—	2.67	—
e	—	5.33	—
$e1$	—	8.61	—
F	—	1.99	—
G	0.89	—	—
L	3.87	3.99	4.11
L1	10.42	10.54	10.66

Notes: ① Dimension includes metallization flash.

② Dimension does not include metallization flash.

Note: All terminals are isolated from the case.

**Figure 1c Package Configuration and Terminal Connection of SMD-1 type package
(JAXA R 2SJ1A05 and 2SJ1A11)**



Symbol	Dimension (mm)		
	Min	Typ	Max
A	—	—	
A1	0.254	0.381	0.508
b	2.29	2.415	2.54
b1	7.14	7.265	7.39
C	0.76	—	—
D	7.40	7.52	7.64
E	10.04	10.16	10.28

Symbol	Dimension (mm)		
	Min	Typ	Max
	—	1.905	—
	—	3.81	—
	—	5.52	—
F	—	1.65	—
G	0.762	—	—
L	2.93	3.05	3.17
L1	5.59	5.715	5.84

Notes: ① Dimension includes metallization flash.
② Dimension does not include metallization flash.

Note: All terminals are isolated from the case.

**Figure 1d Package Configuration and Terminal Connection of SMD-0.5 type package
(JAXA R 2SJ1A06 and 2SJ1A12)**

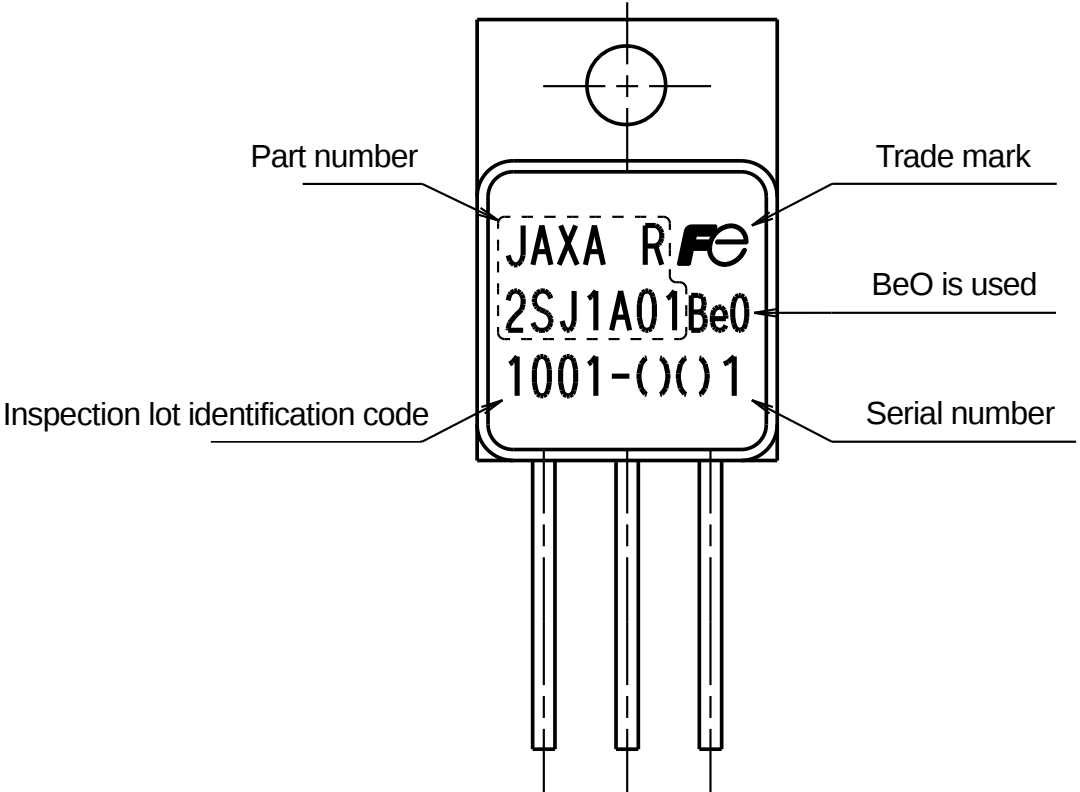


Figure 2a Markings (TO-254)
(JAXA R 2SJ1A01, 2SJ1A02, 2SJ1A03,
2SJ1A07, 2SJ1A08 and 2SJ1A09)

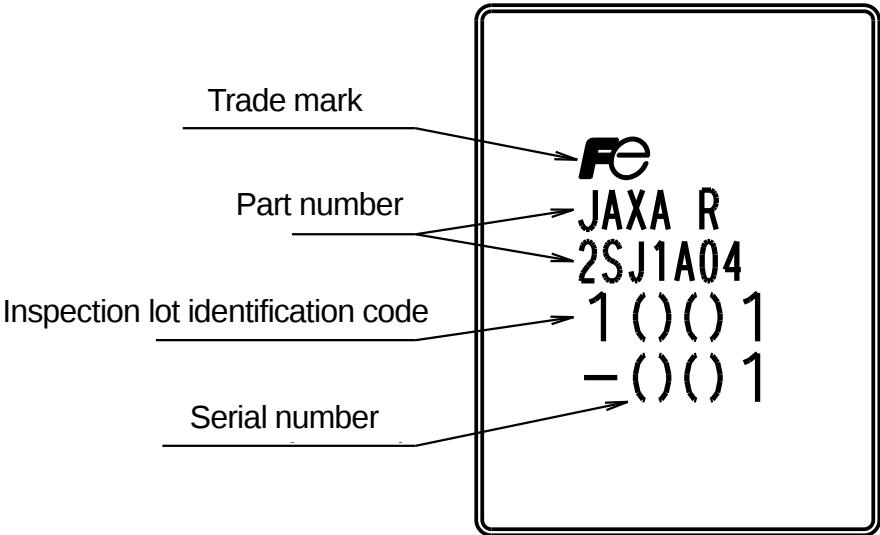


Figure 2b. Markings (SMD-2)
(JAXA R 2SJ1A04 and 2SJ1A10)

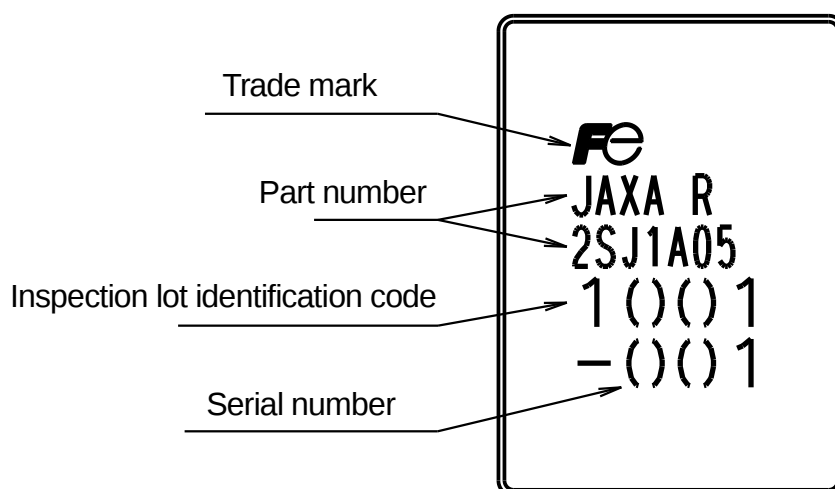


Figure 2c. Markings (SMD-1)
(JAXA R 2SJ1A05 and 2SJ1A11)

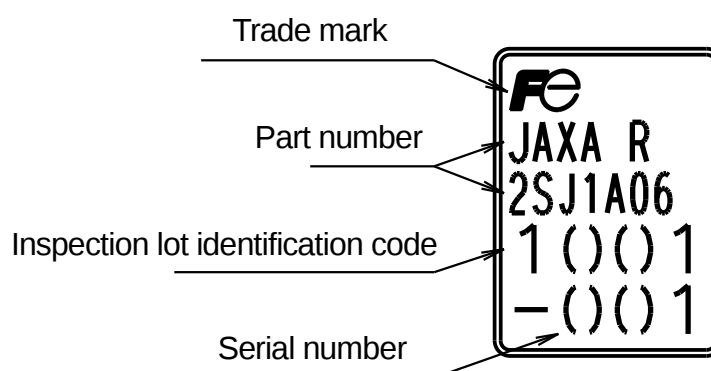


Figure 2d. Markings (SMD-0.5)
(JAXA R 2SJ1A06 and 2SJ1A12)

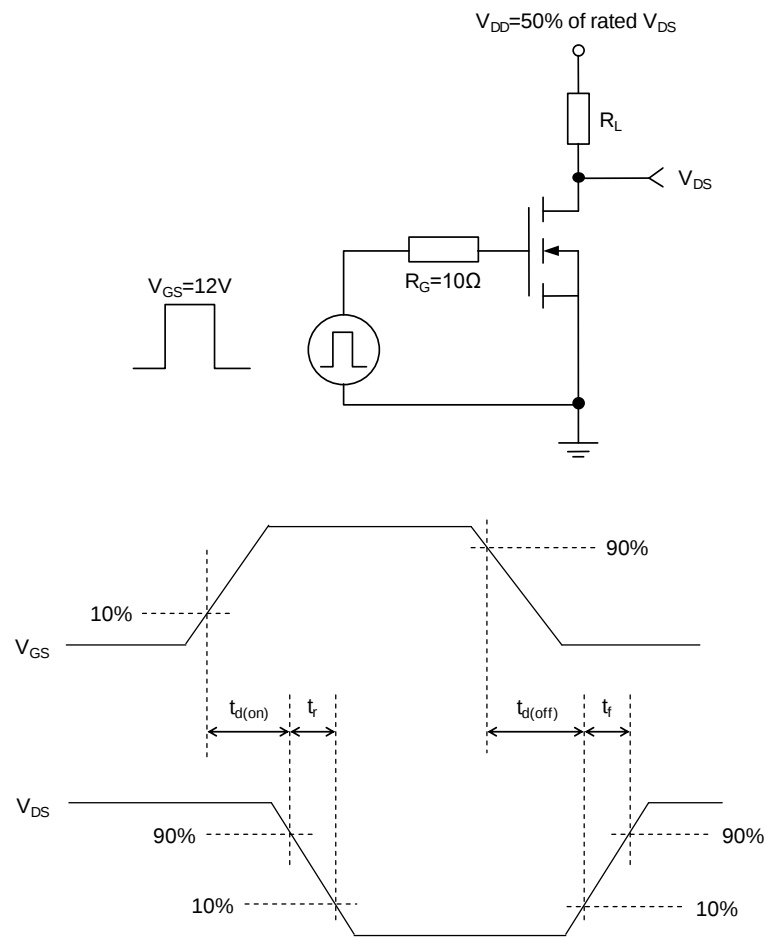


Figure 3. Switching Time Test Circuit and Waveforms

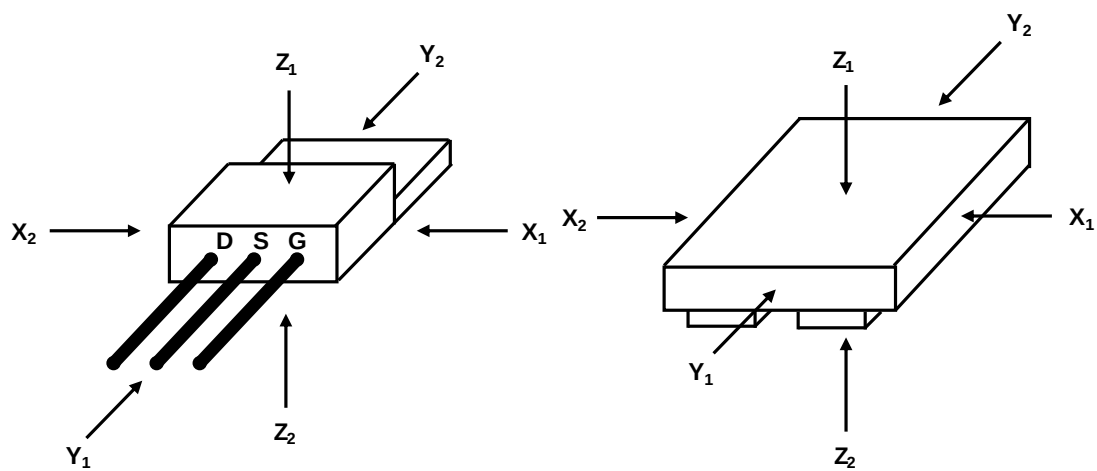


Figure 4. Orientation of the Device

JAXA R 2SJ1A01

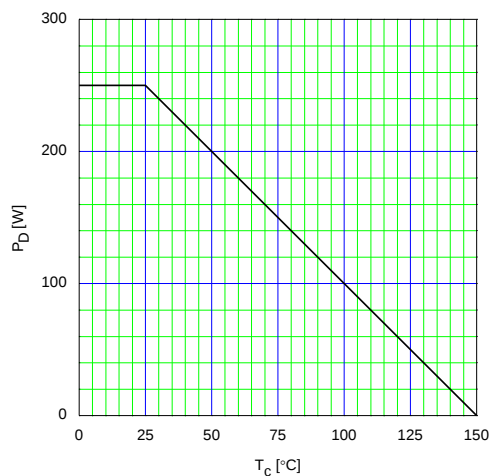


Fig. 5 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A01

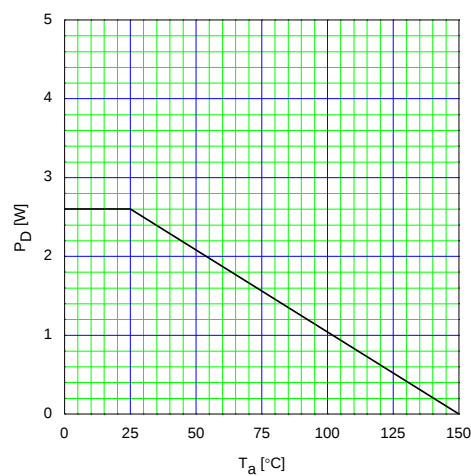


Fig. 6 Allowable Power Dissipation P_D – Ambient Temperature T_a

JAXA R 2SJ1A01

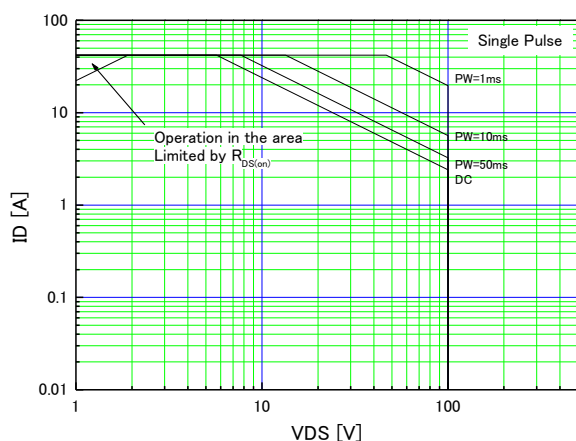


Fig. 7 Maximum Safe Operating Area

JAXA R 2SJ1A02

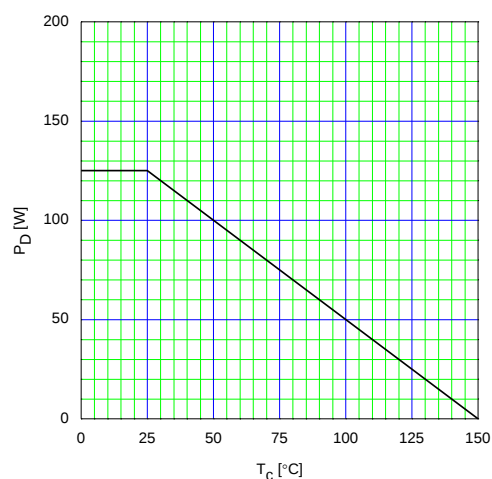


Fig. 8 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A02

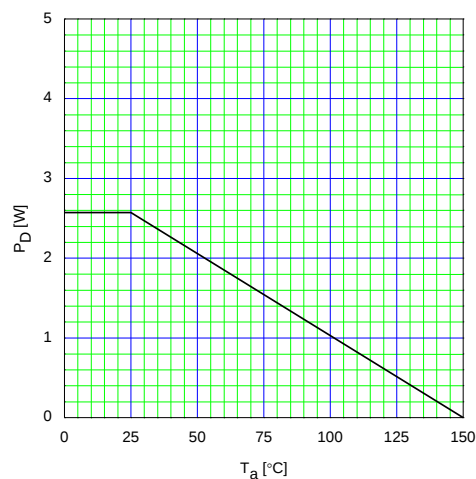


Fig. 9 Allowable Power Dissipation P_D – Ambient Temperature T_a

JAXA R 2SJ1A02

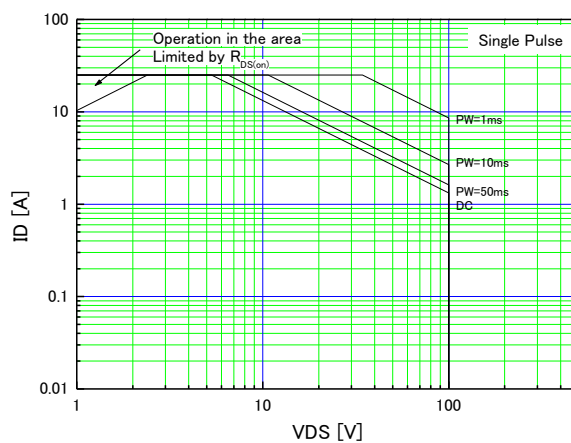


Fig. 10 Maximum Safe Operating Area

JAXA R 2SJ1A03

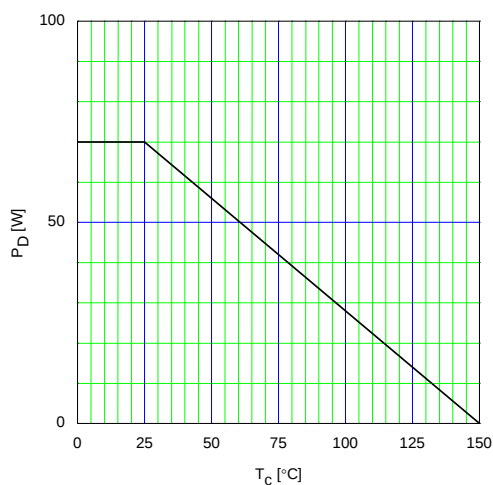


Fig. 11 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A03

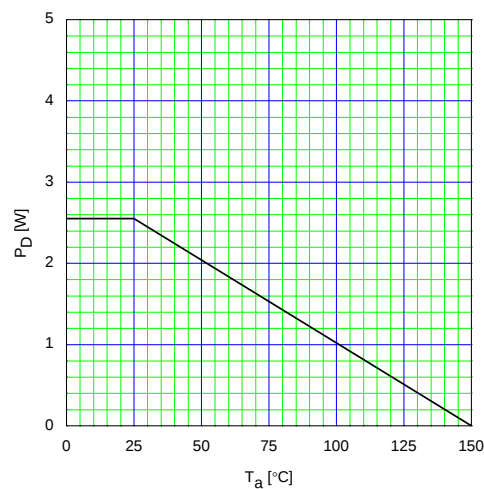


Fig. 12 Allowable Power Dissipation P_D – Ambient Temperature T_a

JAXA R 2SJ1A03

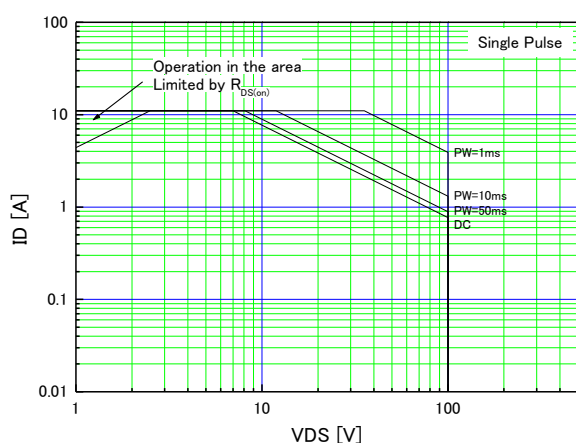


Fig. 13 Maximum Safe Operating Area

JAXA R 2SJ1A04

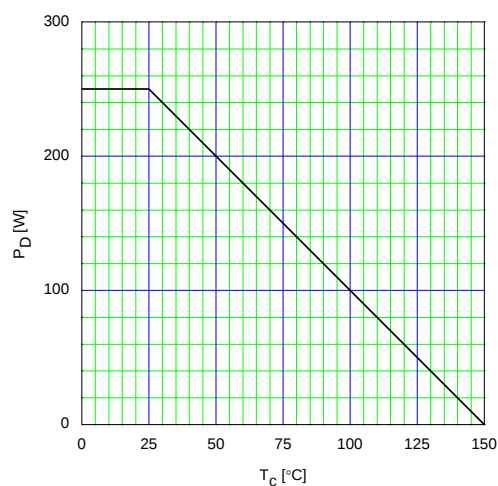


Fig. 14 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A04

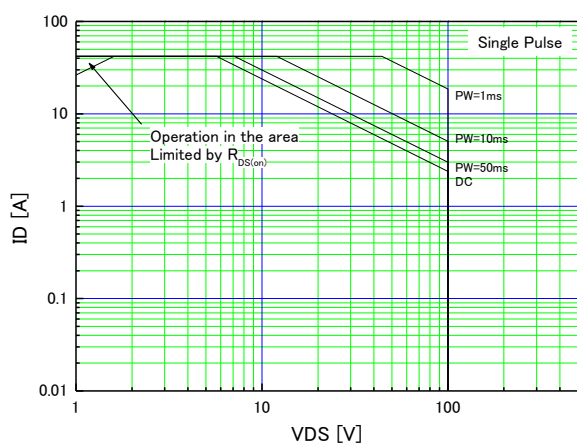


Fig. 15 Maximum Safe Operating Area

JAXA R 2SJ1A05

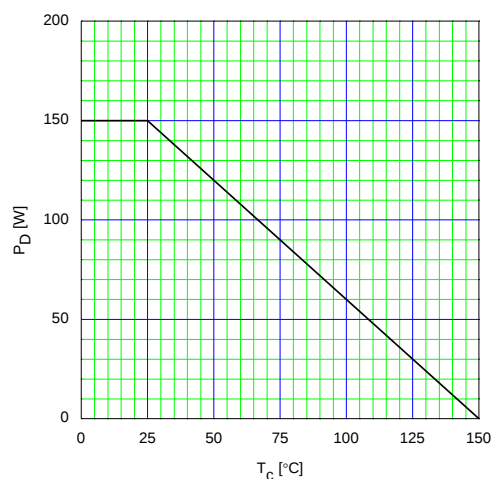


Fig. 16 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A05

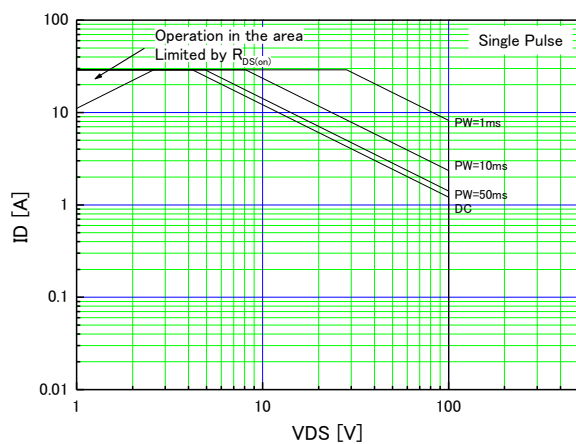


Fig. 17 Maximum Safe Operating Area

JAXA R 2SJ1A06

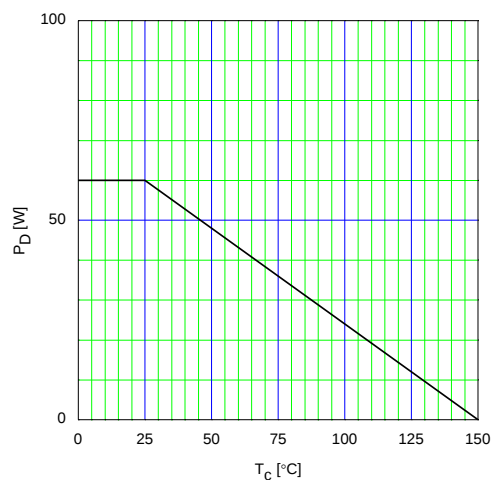


Fig. 18 Allowable Power Dissipation P_D – Case Surface Temperature T_c

JAXA R 2SJ1A06

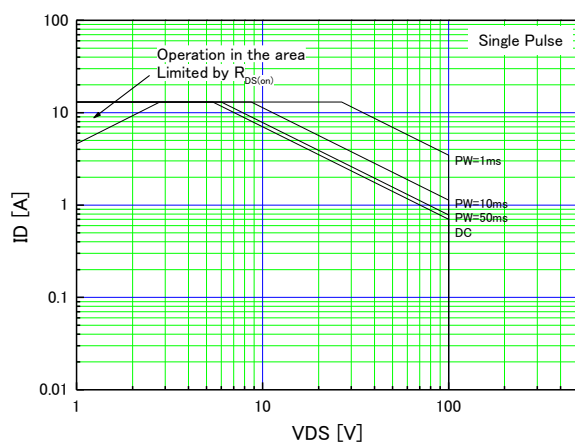


Fig. 19 Maximum Safe Operating Area

JAXA R 2SJ1A07

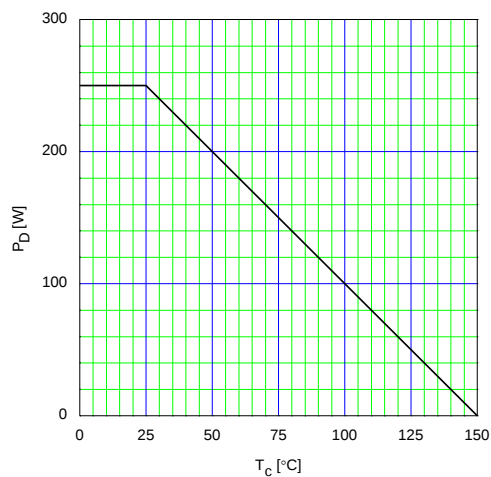


Fig. 20 Allowable Power Dissipation P_D – Case Surface Temperature T_c

JAXA R 2SJ1A07

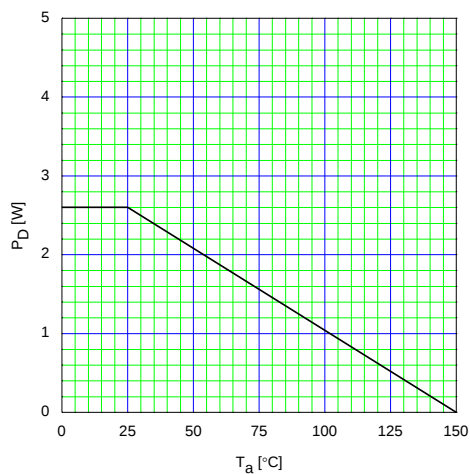


Fig. 21 Allowable Power Dissipation P_D – Ambient Temperature T_a

JAXA R 2SJ1A07

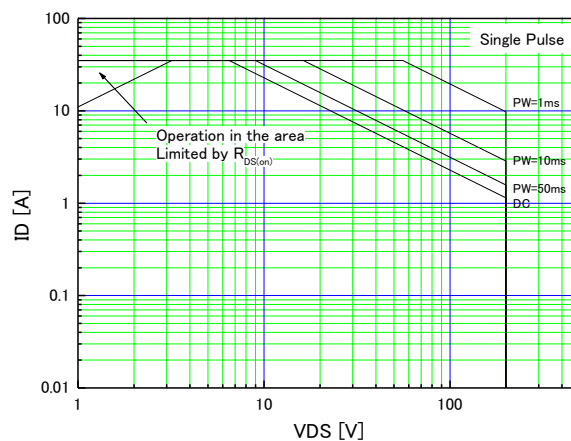


Fig. 22 Maximum Safe Operating Area

JAXA R 2SJ1A08

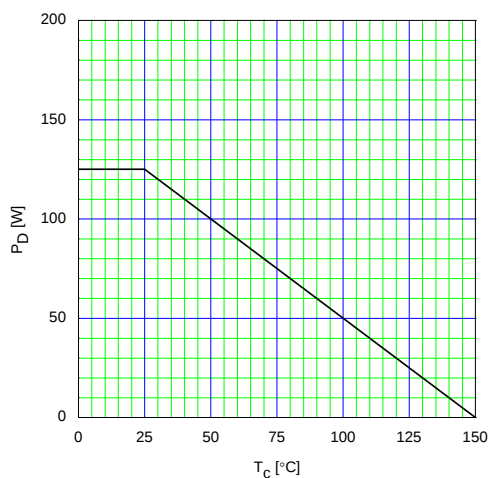


Fig. 23 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A08

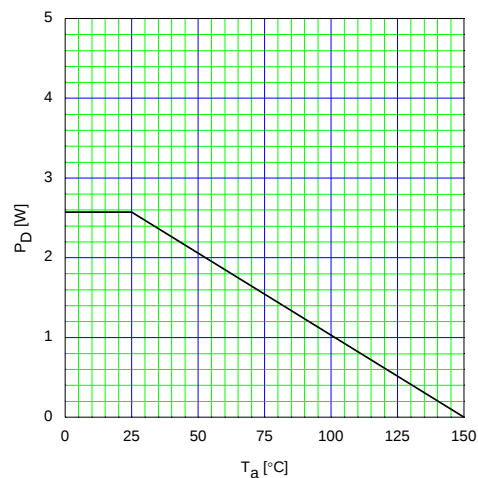


Fig. 24 Allowable Power Dissipation P_D – Ambient Temperature T_a

JAXA R 2SJ1A08

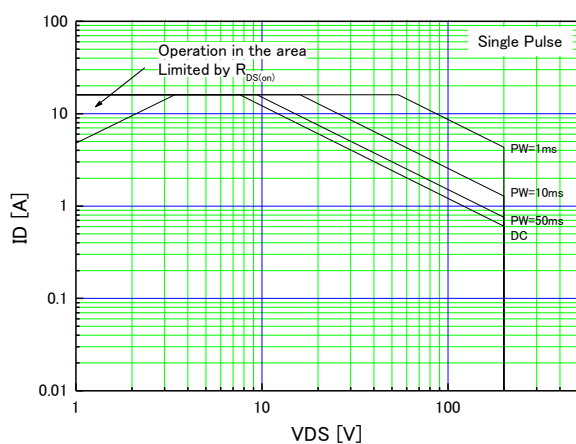


Fig. 25 Maximum Safe Operating Area

JAXA R 2SJ1A09

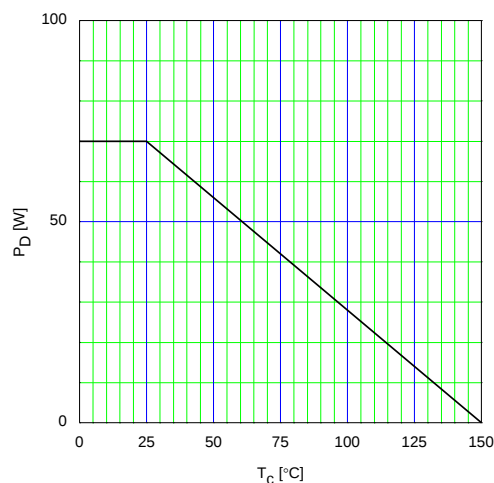


Fig. 26 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A09

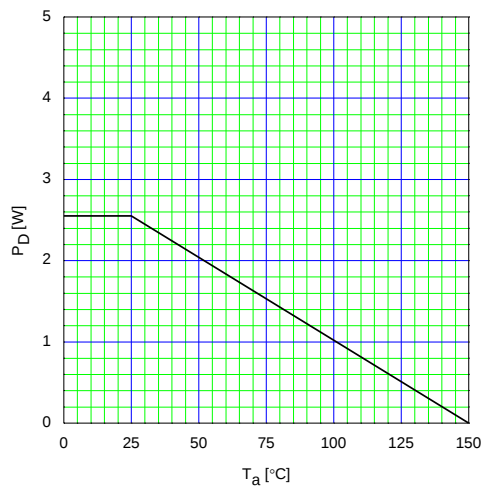


Fig. 27 Allowable Power Dissipation P_D – Ambient Temperature T_a

JAXA R 2SJ1A09

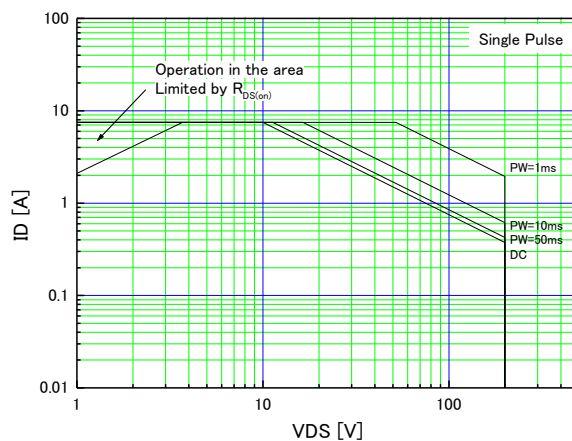


Fig. 28 Maximum Safe Operating Area

JAXA R 2SJ1A10

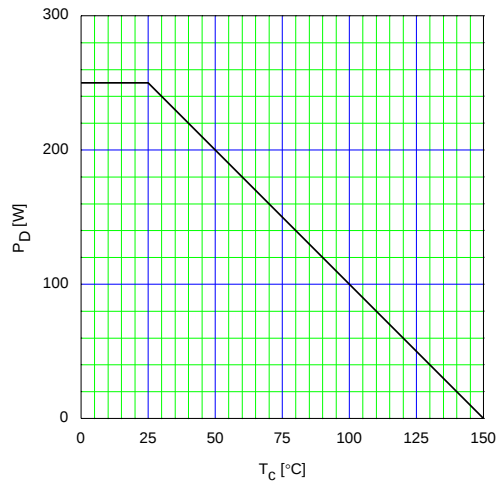


Fig. 29 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A10

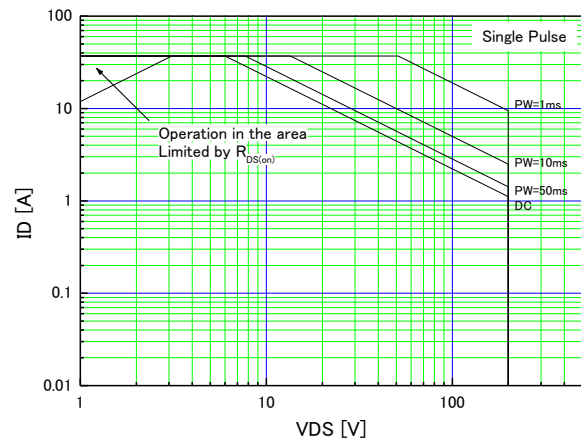


Fig. 30 Maximum Safe Operating Area

JAXA R 2SJ1A11

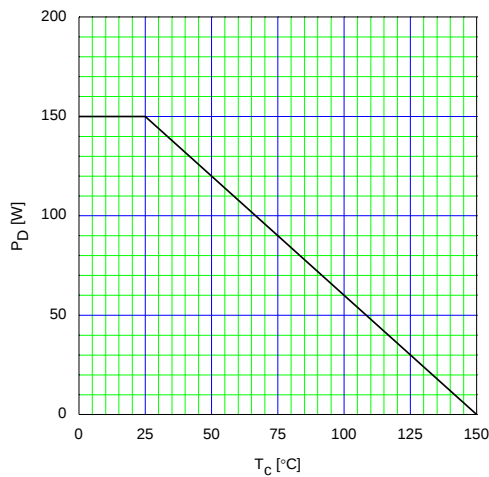


Fig. 31 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A11

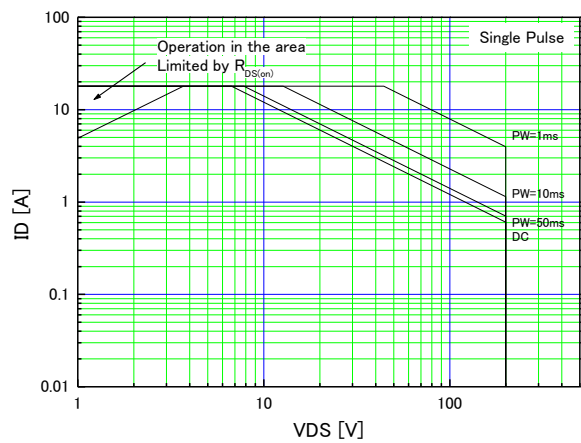


Fig. 32 Maximum Safe Operating Area

JAXA R 2SJ1A12

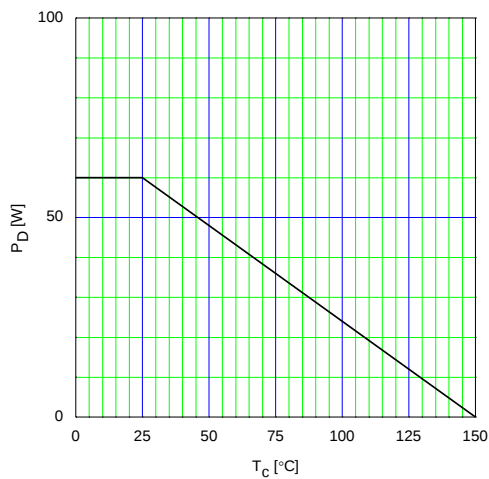


Fig. 33 Allowable Power Dissipation P_D – Case Surface Temperature T_C

JAXA R 2SJ1A12

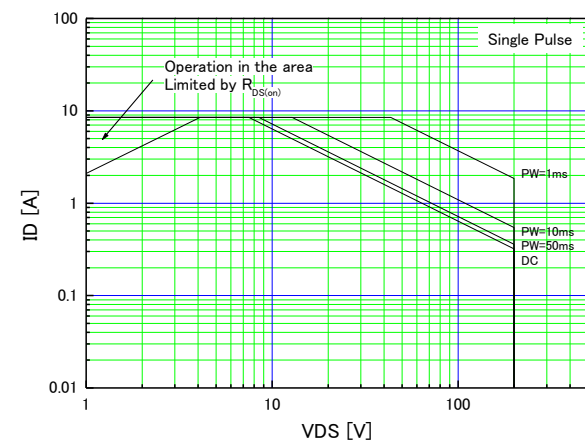


Fig. 34 Maximum Safe Operating Area